

L Number	Hits	Search Text	DB	Time stamp
1	26367	bipolar adj transistor\$2	USPAT	2003/09/23 14:10
2	1225	((bipolar adj transistor\$2) and ((silicon adj (oxide or dioxide)) with oxidation)) and substrate and base\$2	USPAT	2003/09/23 14:14
3	1016	((bipolar adj transistor\$2) and ((silicon adj (oxide or dioxide)) with oxidation)) and substrate and base\$2	USPAT	2003/09/23 14:11
4	845	((bipolar adj transistor\$2) and ((silicon adj (oxide or dioxide)) with oxidation)) and substrate and base\$2 and (opening or hole\$2 or aperture\$2)	USPAT	2003/09/23 14:13
5	659	((bipolar adj transistor\$2) and ((silicon adj (oxide or dioxide)) with oxidation)) and substrate and base\$2 and (opening or hole\$2 or aperture\$2) and ((silicon adj nitride) or sin)	USPAT	2003/09/23 14:13
6	379	((bipolar adj transistor\$2) and ((silicon adj (oxide or dioxide)) with oxidation)) and substrate and base\$2 and (opening or hole\$2 or aperture\$2) and ((silicon adj nitride) or sin) with etch\$4	USPAT	2003/09/23 14:14
7	212	((bipolar adj transistor\$2) and ((silicon adj (oxide or dioxide)) with oxidation)) and substrate and base\$2 and (opening or hole\$2 or aperture\$2) and ((silicon adj nitride) or sin) with etch\$4) and ((silicon adj (oxide or dioxide)) with second)	USPAT	2003/09/23 14:15
8	178	((bipolar adj transistor\$2) and ((silicon adj (oxide or dioxide)) with oxidation)) and substrate and base\$2 and (opening or hole\$2 or aperture\$2) and ((silicon adj nitride) or sin) with etch\$4) and ((silicon adj (oxide or dioxide)) with second)) and emitter	USPAT	2003/09/23 14:17
9	147	((bipolar adj transistor\$2) and ((silicon adj (oxide or dioxide)) with oxidation)) and substrate and base\$2 and (opening or hole\$2 or aperture\$2) and ((silicon adj nitride) or sin) with etch\$4) and ((silicon adj (oxide or dioxide)) with second)) and emitter and epitaxial	USPAT	2003/09/23 14:48
10	10	((bipolar adj transistor\$2) and ((silicon adj (oxide or dioxide)) with oxidation)) and substrate and base\$2 and (opening or hole\$2 or aperture\$2) and ((silicon adj nitride) or sin) with etch\$4) and ((silicon adj (oxide or dioxide)) with second)) and emitter and epitaxial) and (wet adj etch\$4) and undercut\$4	USPAT	2003/09/23 14:49
11	9	((bipolar adj transistor\$2) and ((silicon adj (oxide or dioxide)) with oxidation)) and substrate and base\$2 and (opening or hole\$2 or aperture\$2) and ((silicon adj nitride) or sin) with etch\$4) and ((silicon adj (oxide or dioxide)) with second)) and emitter and epitaxial) and (wet adj etch\$4) and undercut\$4 and thermal\$4	USPAT	2003/09/23 14:49
12	1	((bipolar adj transistor\$2) and ((silicon adj (oxide or dioxide)) with oxidation)) and substrate and base\$2 and (opening or hole\$2 or aperture\$2) and ((silicon adj nitride) or sin) with etch\$4) and ((silicon adj (oxide or dioxide)) with second)) and emitter and epitaxial) and (wet adj etch\$4) and undercut\$4 and thermal\$4) and (second adj (oxide or dioxide))	USPAT	2003/09/23 14:50